

# SiPM overview

Samo Korpar

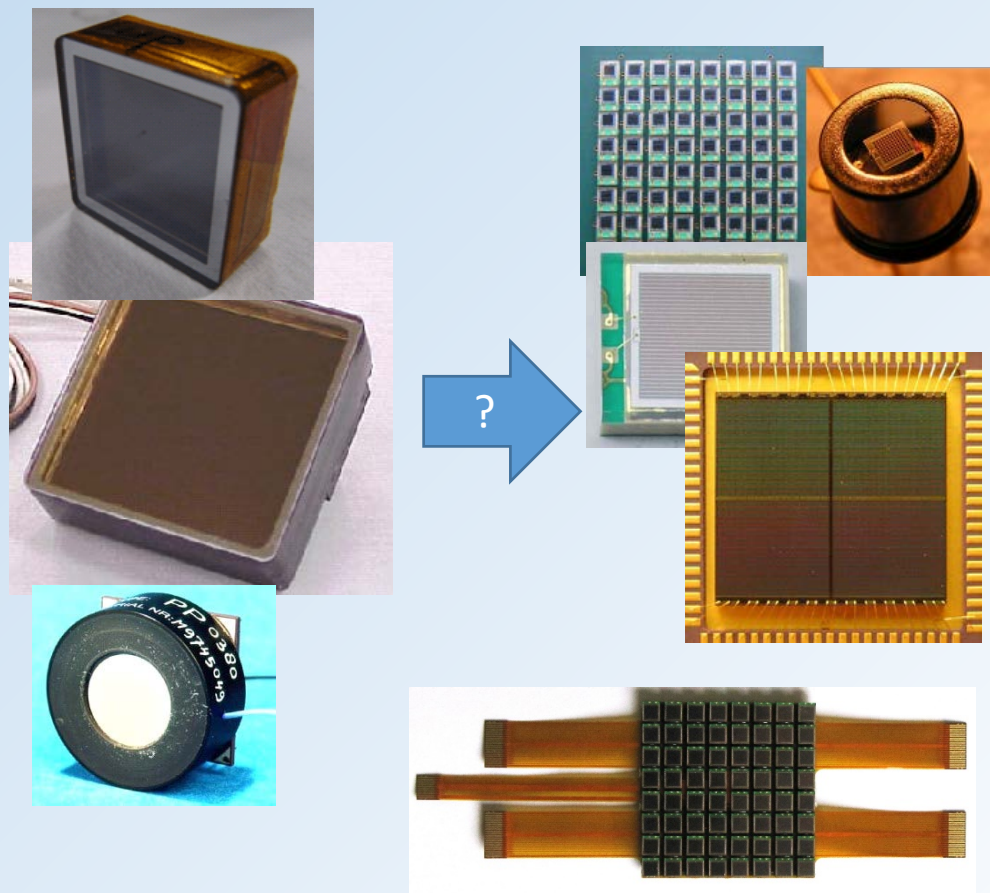
University of Maribor and Jožef Stefan Institute, Ljubljana



DIRC2019, 11-13 September 2019

## Outline:

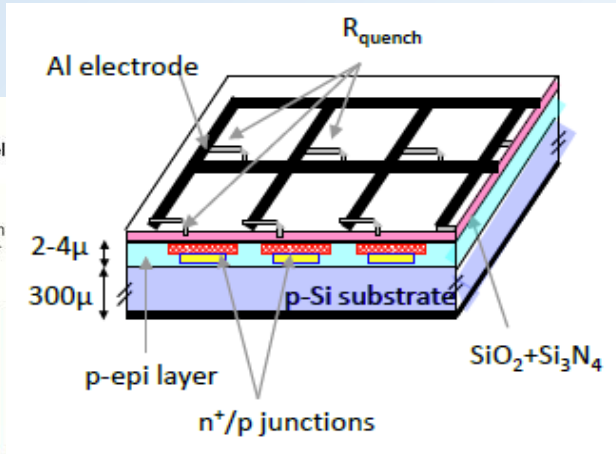
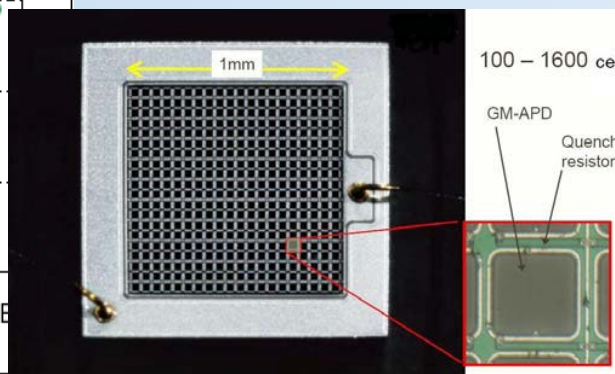
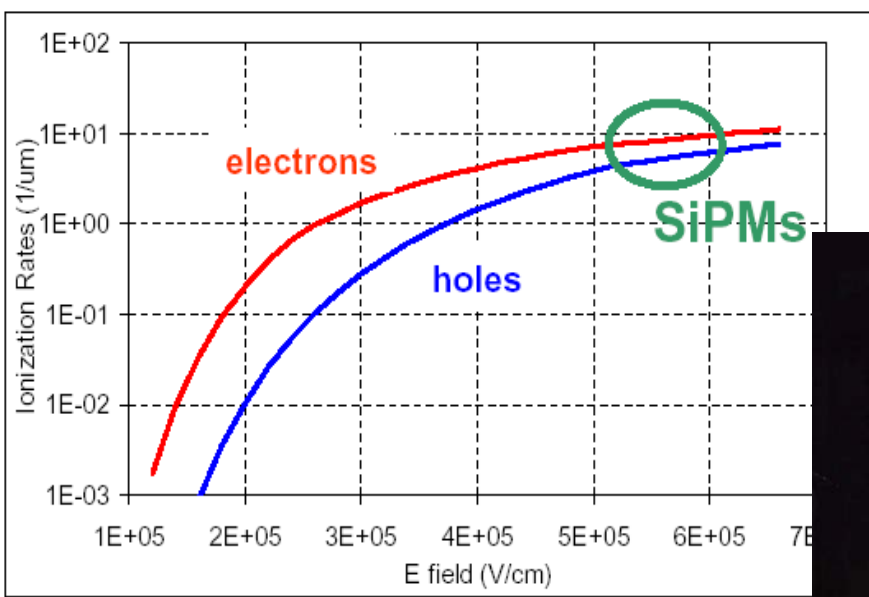
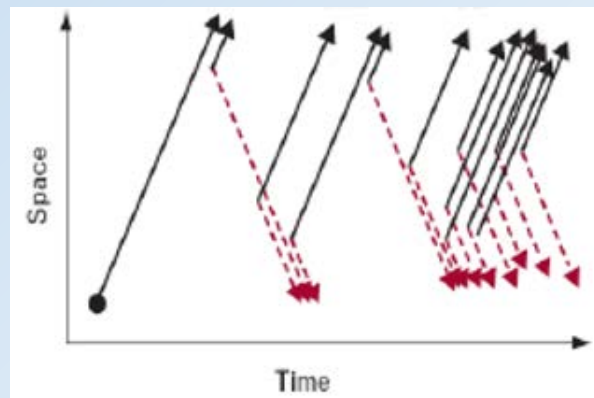
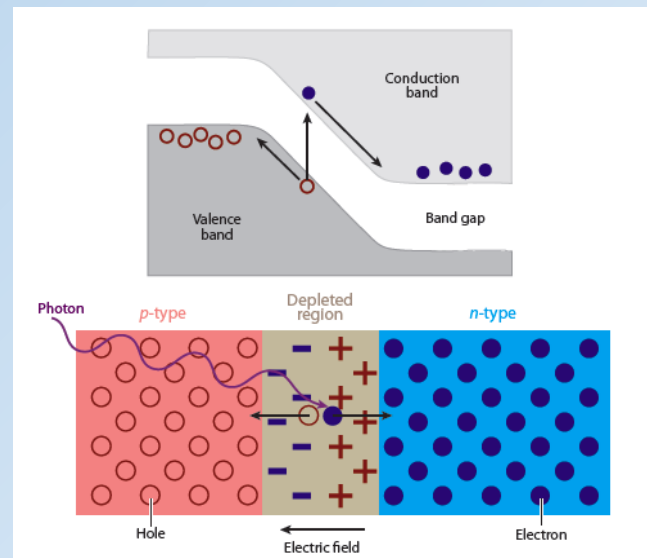
- SiPM basics (operation, PDE, signal gain, noise ...)
- Detection of single Cherenkov photons with SiPM (ARICH, FARICH)
- TOF-PET coincidence timing with Cherenkov light
- Summary



An array of APDs operated in Geiger mode – above APD breakdown voltage (microcells or SPADs – single photon avalanche diodes)

Detection of photons:

- absorbed photon generates electron-hole pair ( $QE, \epsilon$ )
- avalanche is triggered by the carrier in the high field region ( $P_{trig}$ )  $\rightarrow$  signal
- voltage drops below breakdown and avalanche is quenched (passive or active quenching)
- each triggered microcell contributes same amount of charge to the signal



# SiPM: PDE

Three main contributions:

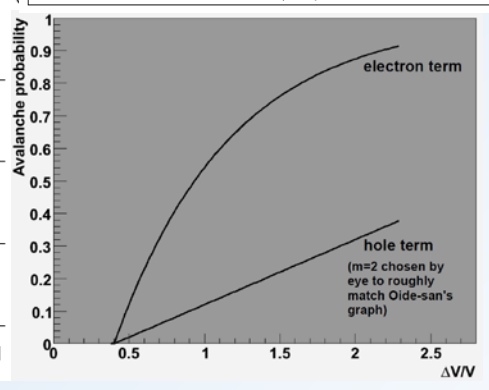
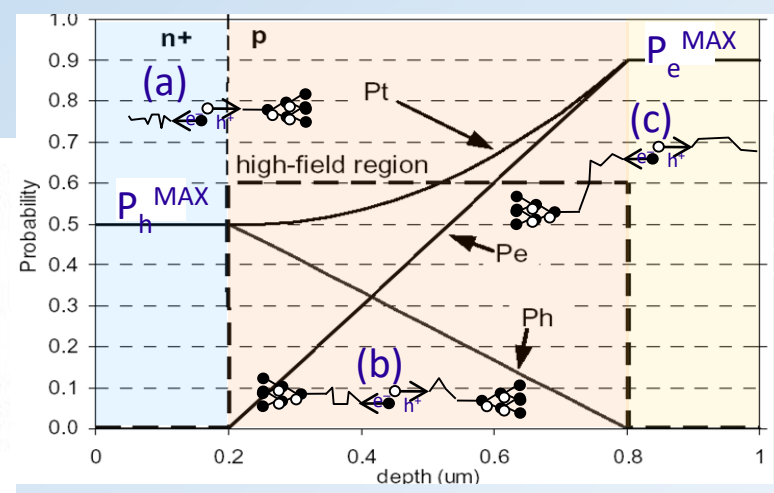
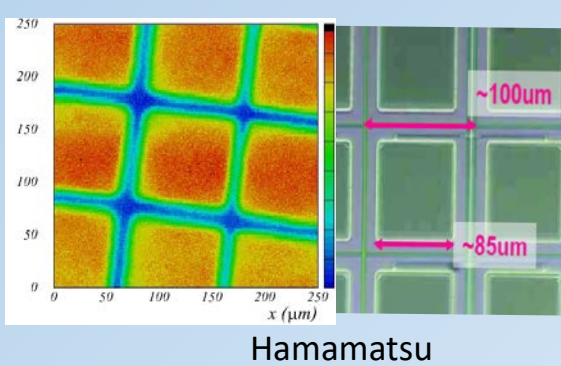
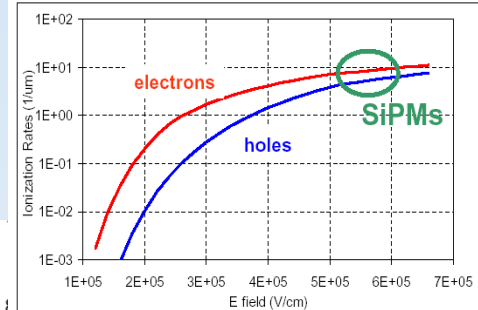
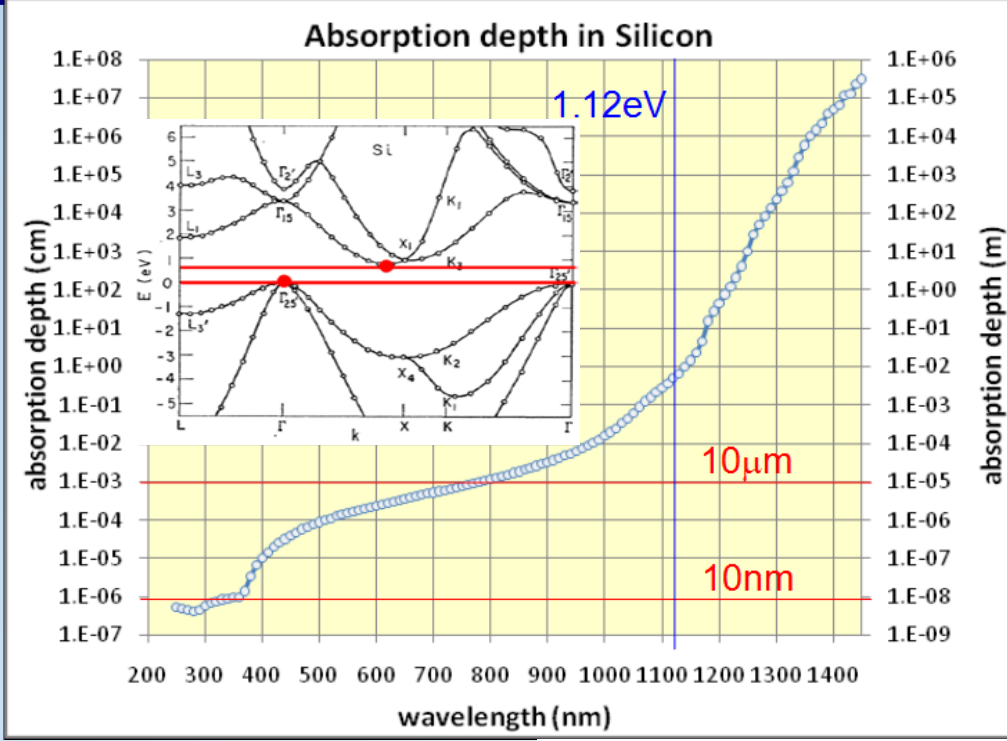
$$PDE = QE \times \epsilon_{geo} \times P_{trig}$$

- QE depends on surface reflections

$$n \approx 5 \rightarrow R \approx \left(\frac{4}{6}\right)^2 = 44\%$$

→ antireflective coating, large variation in absorption length → loss of efficiency:

- absorption at the surface for short  $\lambda$
- transparent for long  $\lambda$
- geometrical efficiency ( $\epsilon_{geo}$ ) – active to total area, reduced by traces, quenching resistors, trenches ...
- triggering probability ( $P_{trig}$ )





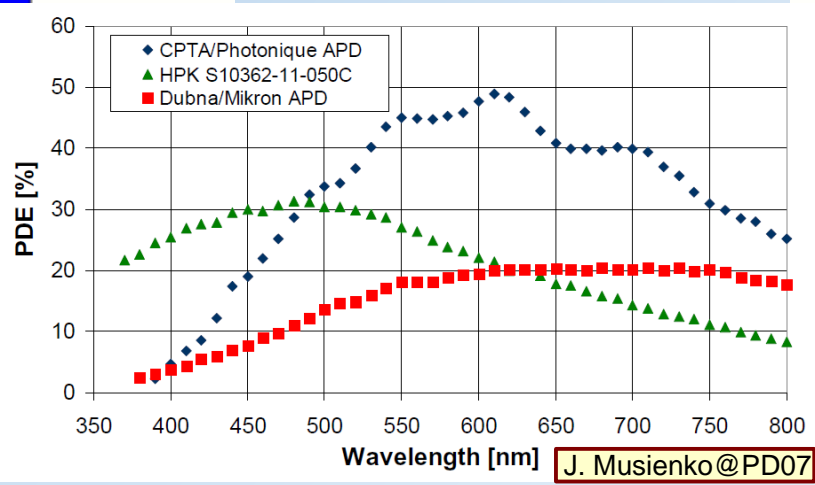
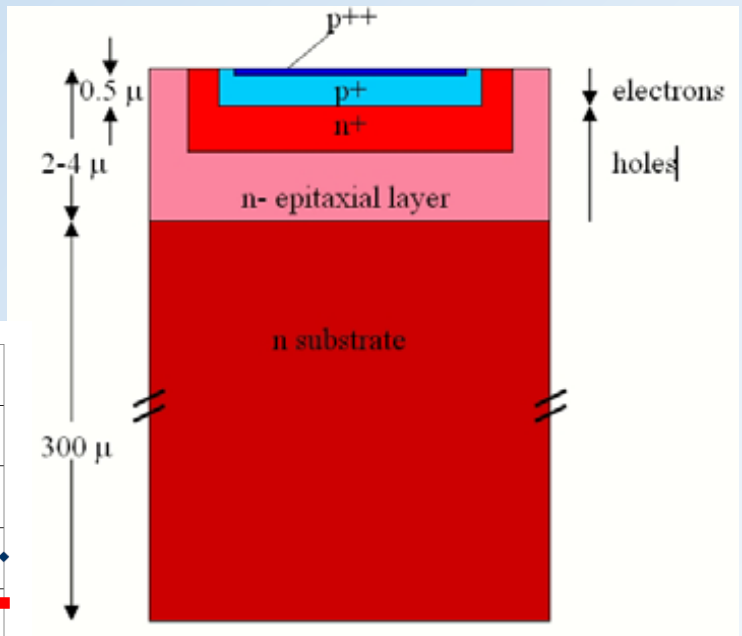
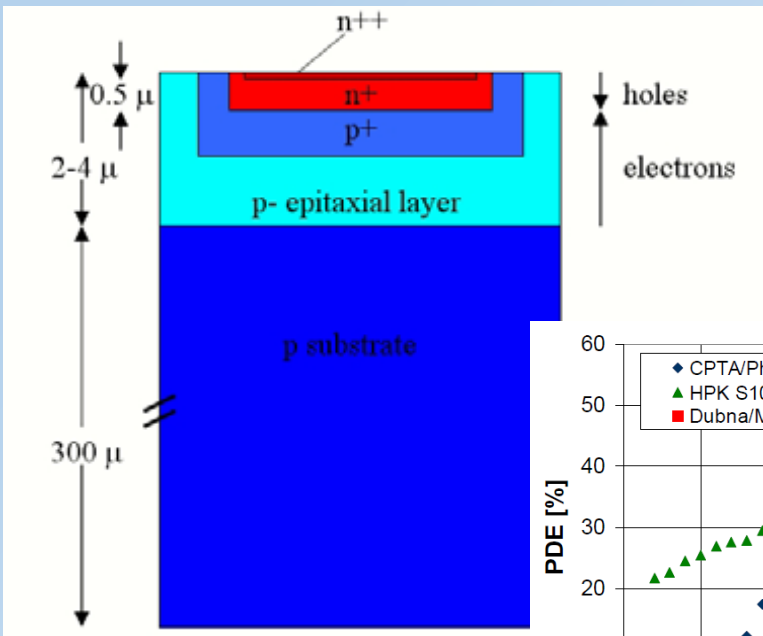
# SiPM: p-on-n vs. n-on-p

## n-on-p: green/red light sensitive:

- electrons drift to Geiger region from substrate and holes from surface side
- higher dark count rate – most of the thermally generated carriers arriving to Geiger region are electrons

## p on n - green/blue light sensitive:

- electrons drift to Geiger region from surface and holes from substrate side
- lower dark count rate – most of the thermally generated carriers arriving to Geiger region are electrons



J. Musienko@PD07

# SiPM: signal basics

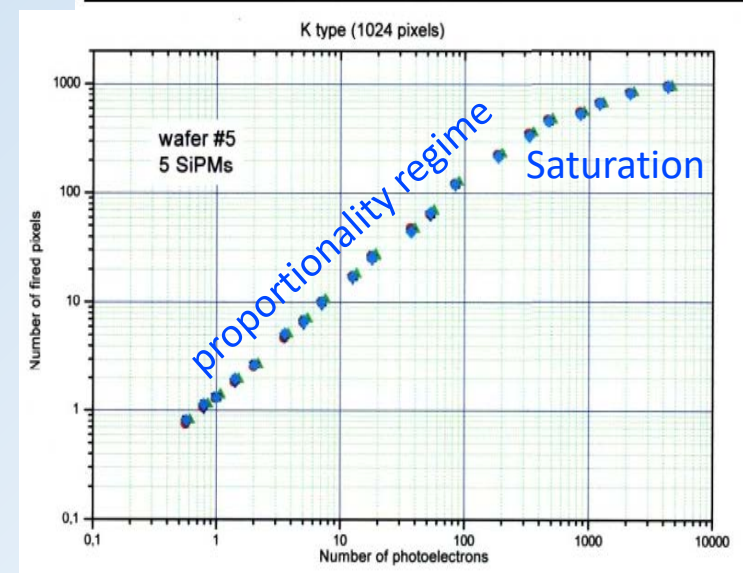
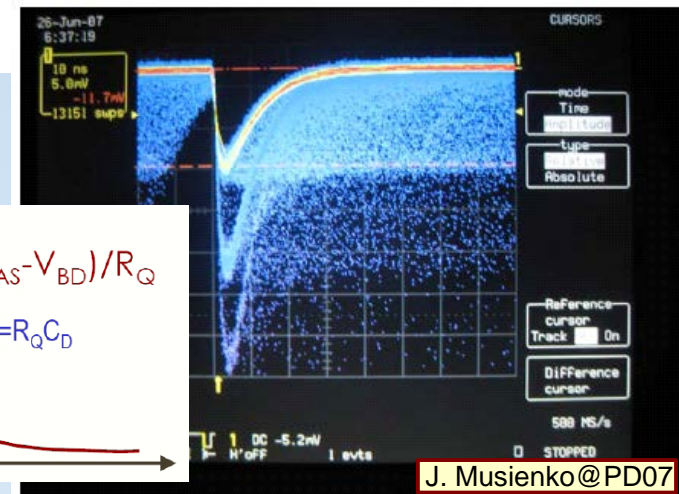
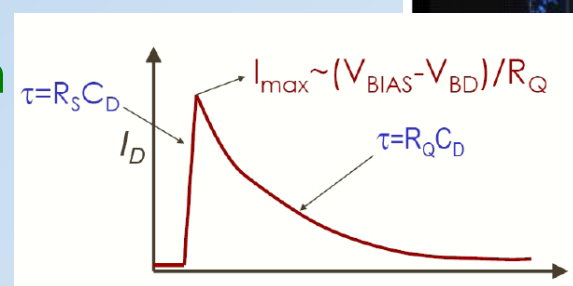
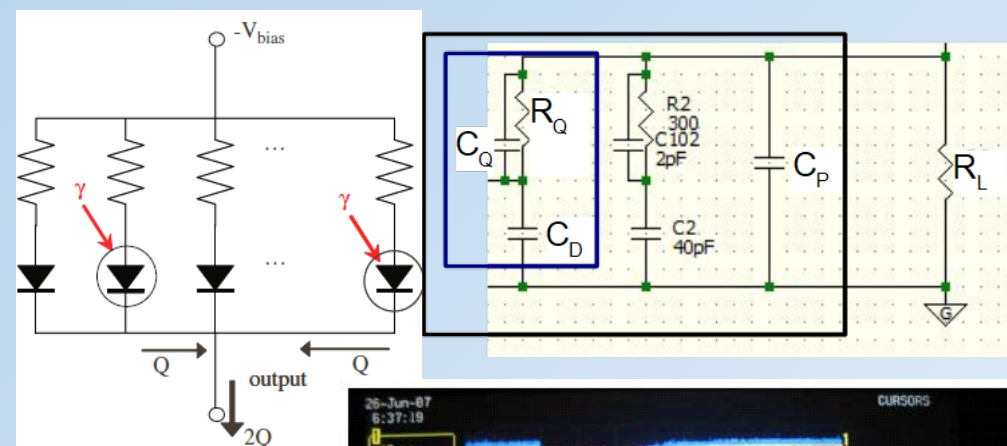
- each triggered microcell contributes equal amount of charge to the signal with a gain

$$G = C_{m.c.} \cdot (V_{bias} - V_{bd}) / e_0$$

- large gain  $\approx 10^5 - 10^7$
- fast rise time  $\approx 100 \text{ ps}$
- relatively short signals, order of  $10 \text{ ns}$
- total signal is the sum of the signals from all microcells – limited linear response to the light pulse intensity (by number of microcells)

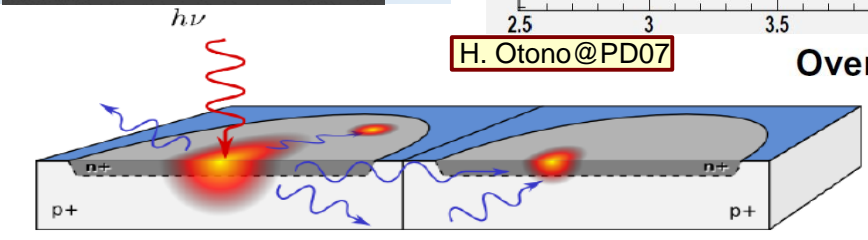
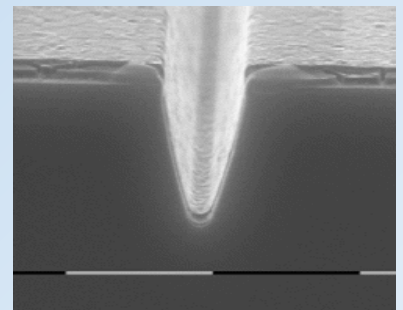
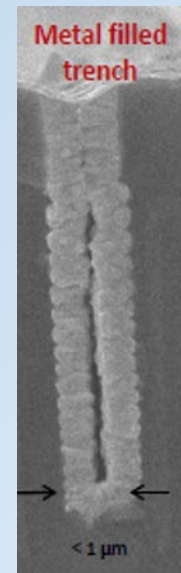
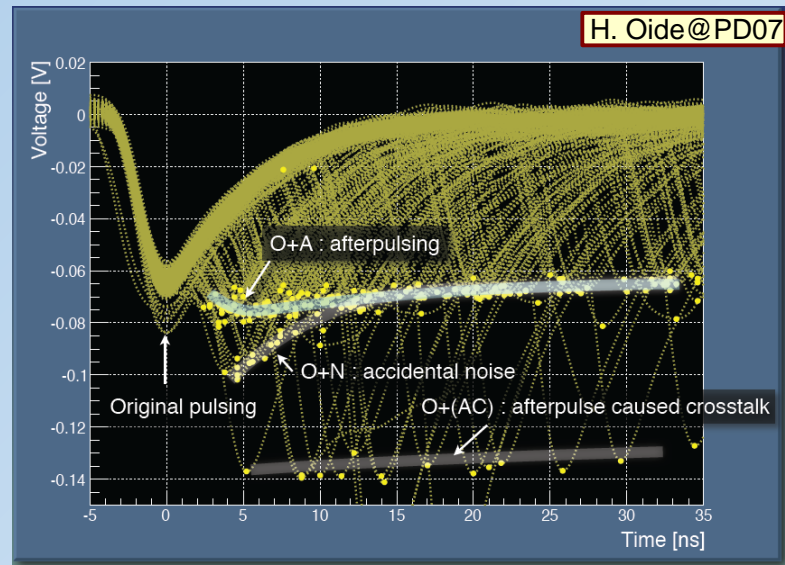
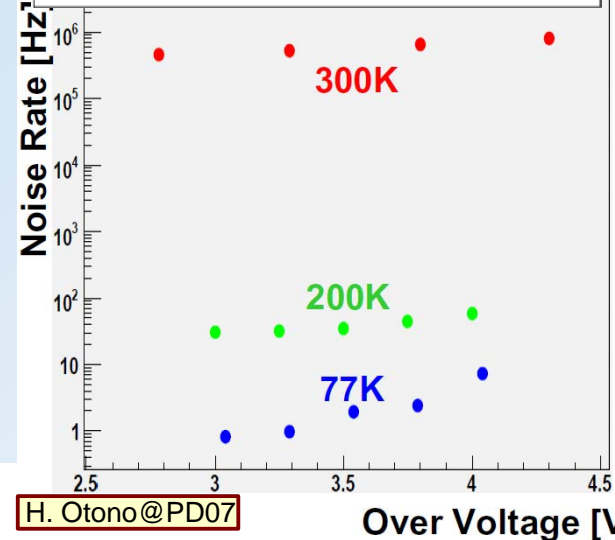
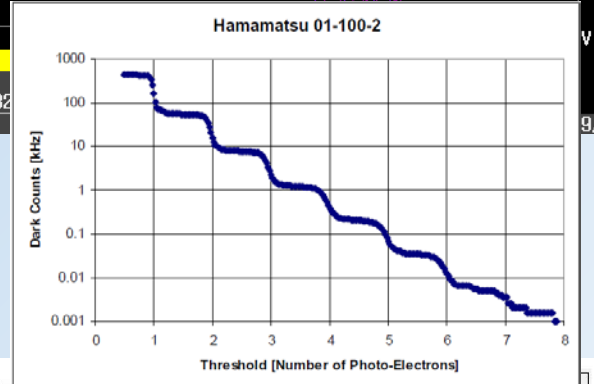
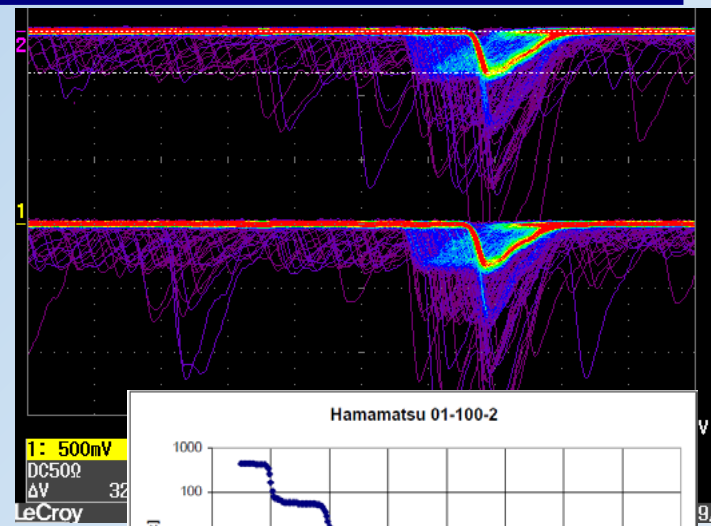
$$n_{fired} = n_{all} \left( 1 - \exp \left( - \frac{n_{phot.} \cdot PDE}{n_{all}} \right) \right)$$

- gain variations with temperature due to a break-down voltage shift, typical  $\frac{dV_{bd}}{dT}$  about  $10 - 100 \text{ mV}/^\circ\text{C}$



# SiPM: noise

- dark counts are produced by thermal generation of carriers, trap assisted tunneling or band gap tunneling
- signal equal to single photon response
- typical rate went from  $\approx 1\text{MHz}/\text{mm}^2$  to below  $\approx 100\text{kHz}/\text{mm}^2$  for more recent samples
- roughly halved for every  $8^\circ\text{C}$
- increases linearly with fluence
- optical cross-talk produced when photons emitted in avalanche initiate signal in neighboring cell, reduced by screening – tranches
- after-pulses produced by trap-release of carriers or delayed arrival of optically induced carrier in the same cell





# SiPM: single "photon" timing

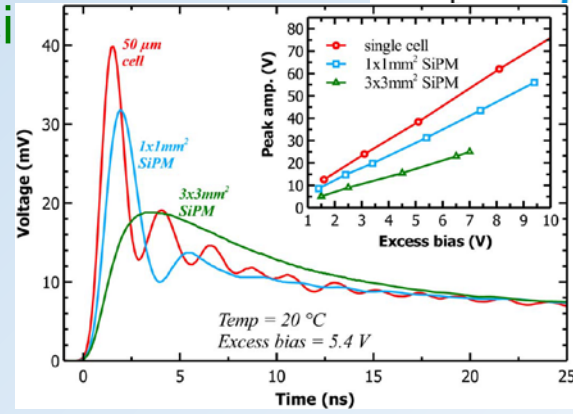
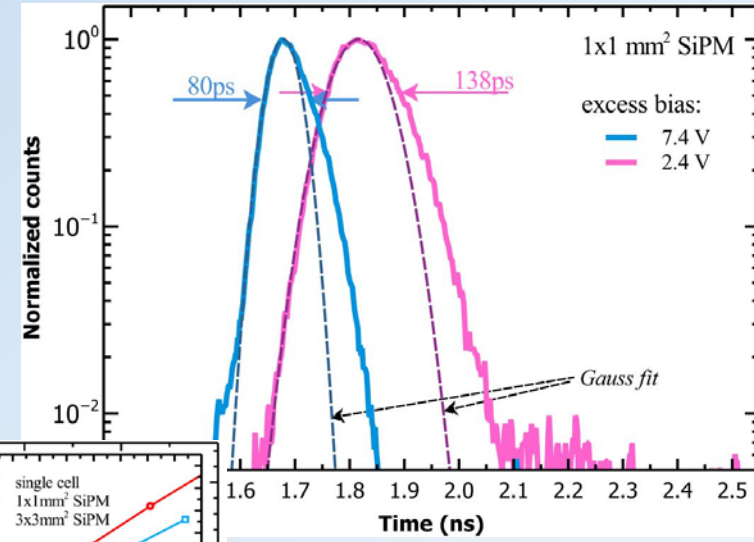
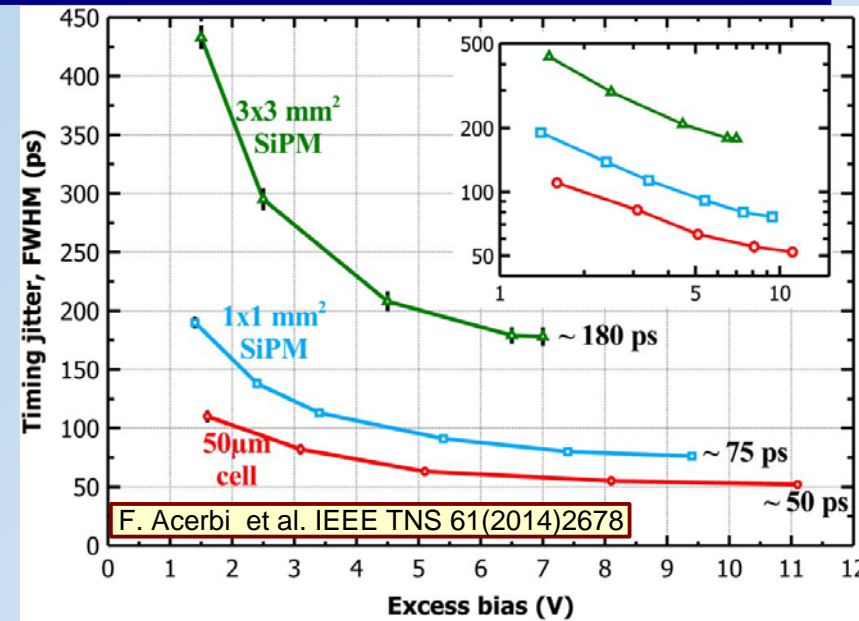
Intrinsic TTS of SiPM microcells is extremely fast,  $< 20$  ps for single SPAD, but timing deteriorates for larger devices. Main contributions:

- nonuniformity within microcell (edges)
- spread between microcells
- overall SiPM capacitance
- $\lambda$  dependence - tails

Comparison of timing properties for single  $50\mu\text{m}$  SPAD,  $1 \times 1 \text{ mm}^2$  and  $3 \times 3 \text{ mm}^2$  SiPMs with the same SPAD for microcells:

- timing improves with higher overvoltage – larger pulses, at the expense of increased SiPM noise
- best timing resolutions for single cell SiPMs are  $\approx 21$  ps,  $32$  ps and  $77$  ps
- TTS deterioration mainly due to larger overall capacitance

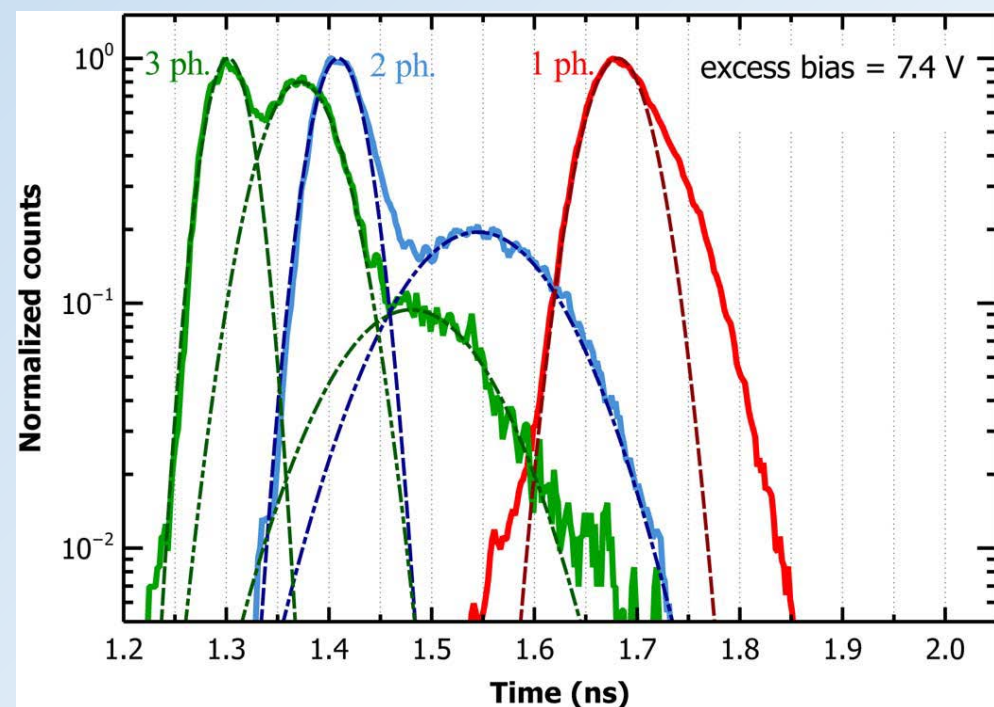
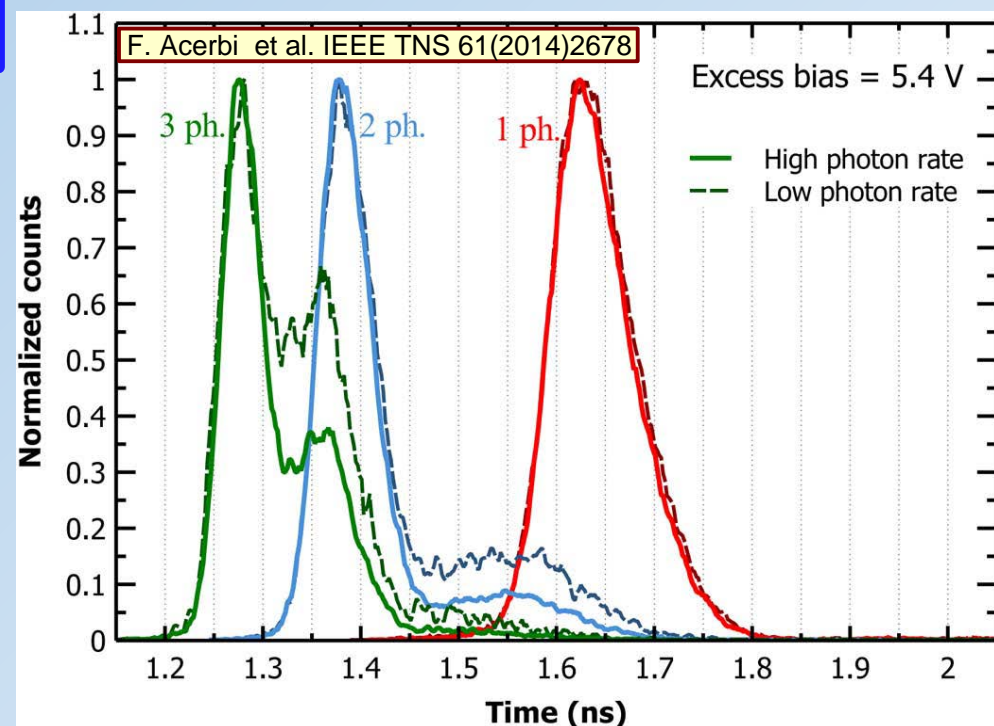
reduced signal slope  $\sigma_t \approx \sigma_e \left( \frac{dU}{dT} \right)^{-1}$



# SiPM: timing for multi-cell signals

Optical cross-talk contribution to multi-cell signals spoils timing distribution – does not scale with  $\frac{1}{N^2}$ :

- two components for 2 m.c. signals:
  - double photon events – proper scaling
  - single photon with cross-talk, timing somewhere between single and double m.c. signals and resolution is worse
- ratio between contributions changes with light intensity confirming optical cross-talk origin
- even more components for larger signals
- may not be such a big effect for DIRC where single photon hits are well spaced in time and 2 m.c. signal would have only cross-talk peak – still worse resolution than sigl m.c. peak.

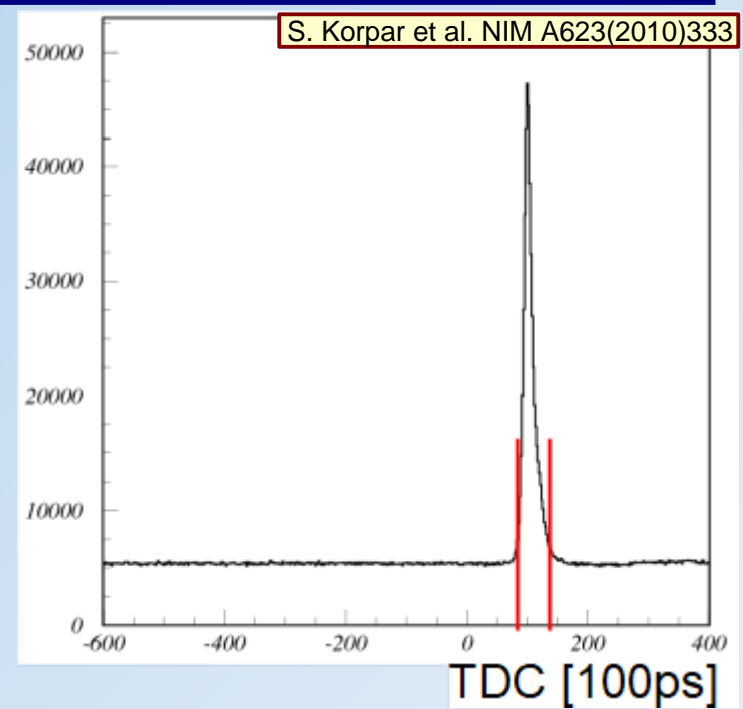
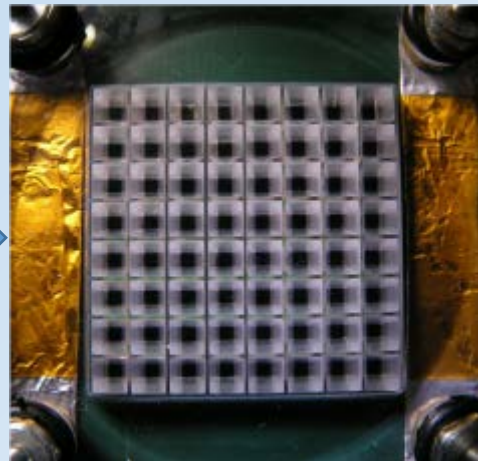
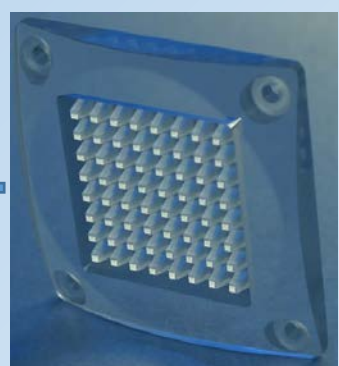
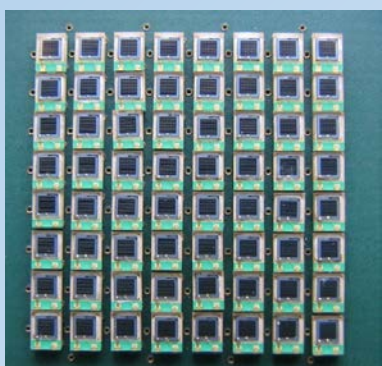
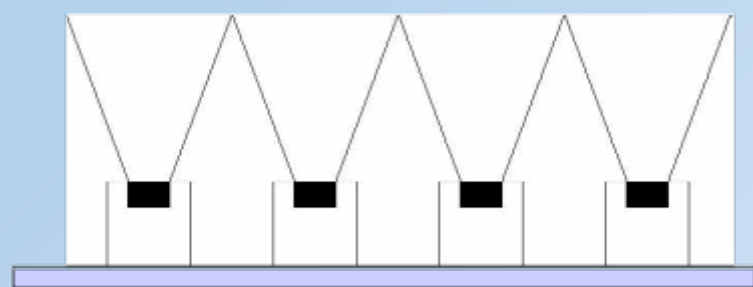




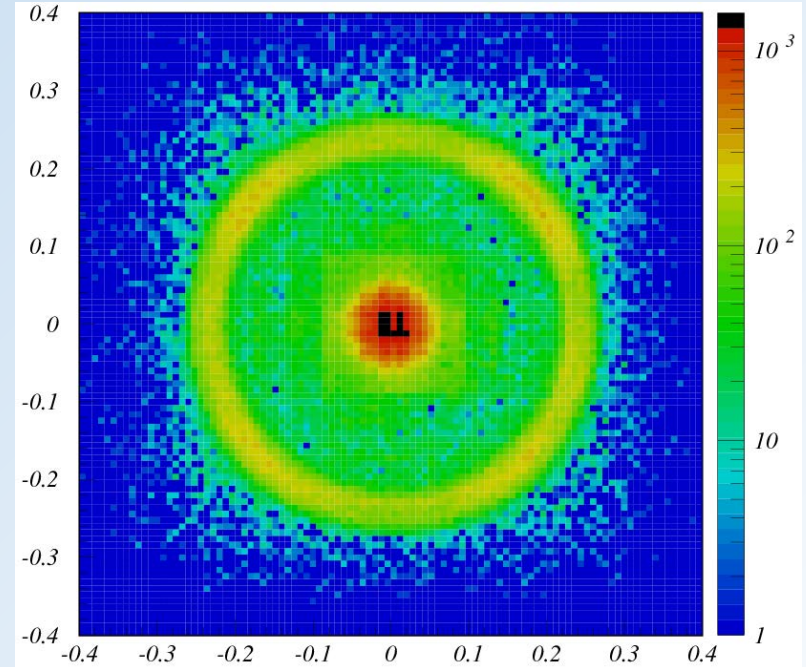
# SiPM RICH: early study

SiPM tests for focusing aerogel RICH, Belle II

- aerogel 1 cm,  $n = 1.03$
- $8 \times 8$  array of Hamamatsu S10362-11-100P
- Improve signal to noise ratio by:
  - narrow time window
  - use of light concentrators
- 3.7 photons/ring detected -  $\approx 18$  expected for 40 mm,  $n = 1.05$  aerogel



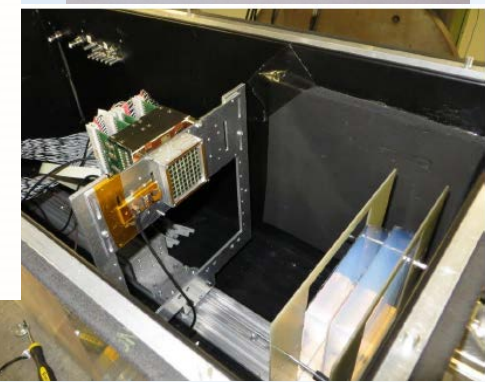
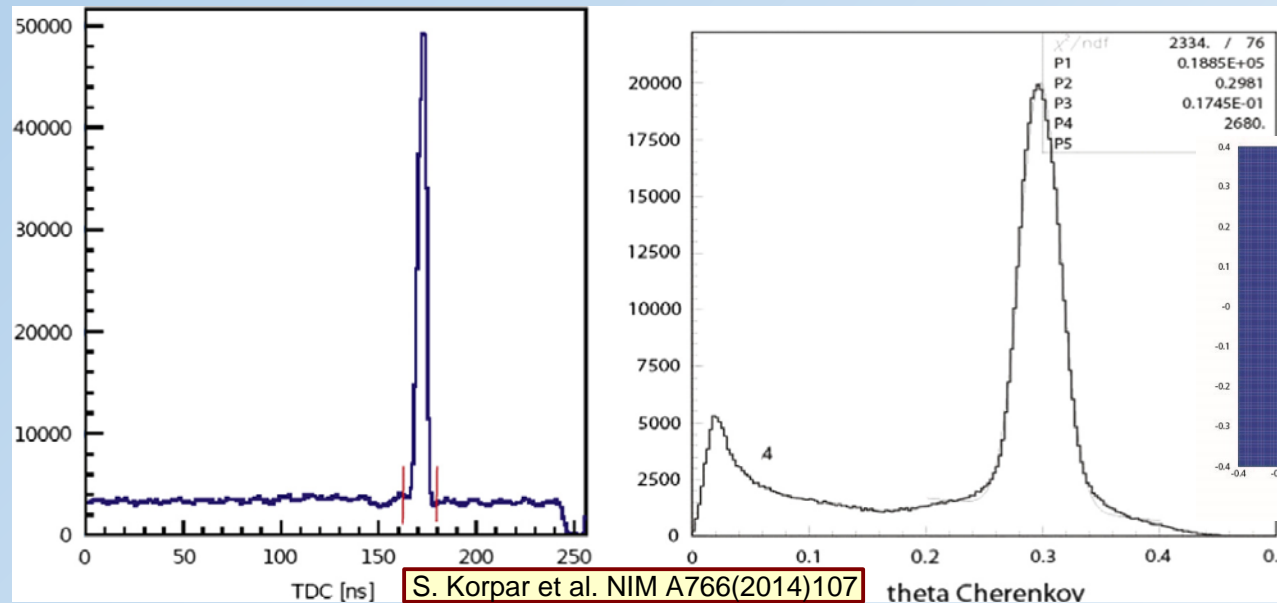
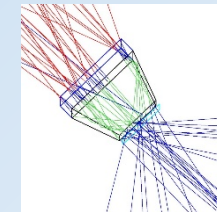
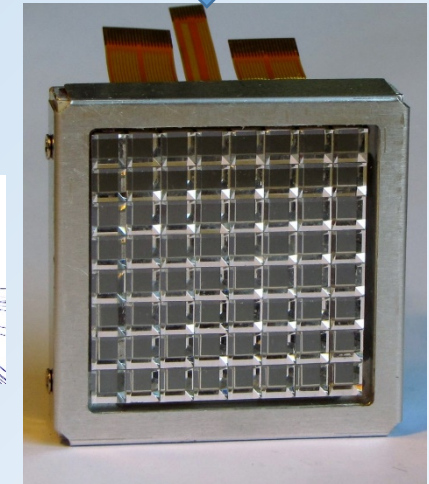
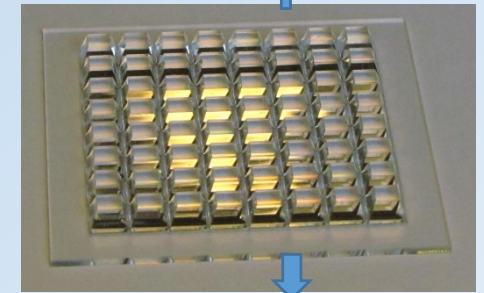
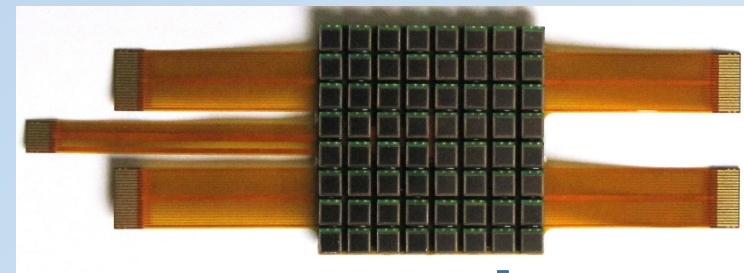
beam test result (1cm,n=1.03)



# SiPM RICH: update

More realistic module prototype to be used for ARICH photon detector.

- Hamamatsu 64 channel MPPC module S11834-3388DF,  $8 \times 8$  array of  $3 \times 3 \text{ mm}^2$  SiPMs @  $5 \text{ mm}$  pitch
- matching array of quartz light concentrators used to
- two  $20 \text{ mm}$  thick aerogel tiles in focusing configuration ( $n = 1.045, 1.055$ )
- tested in  $5 \text{ GeV}$  electron beam at DESY
- 36 hits/ring detected

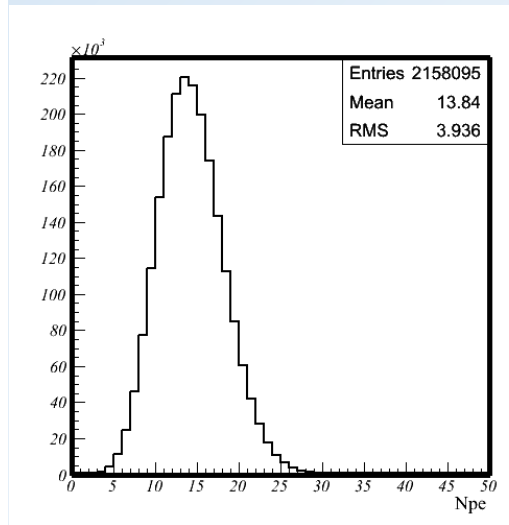
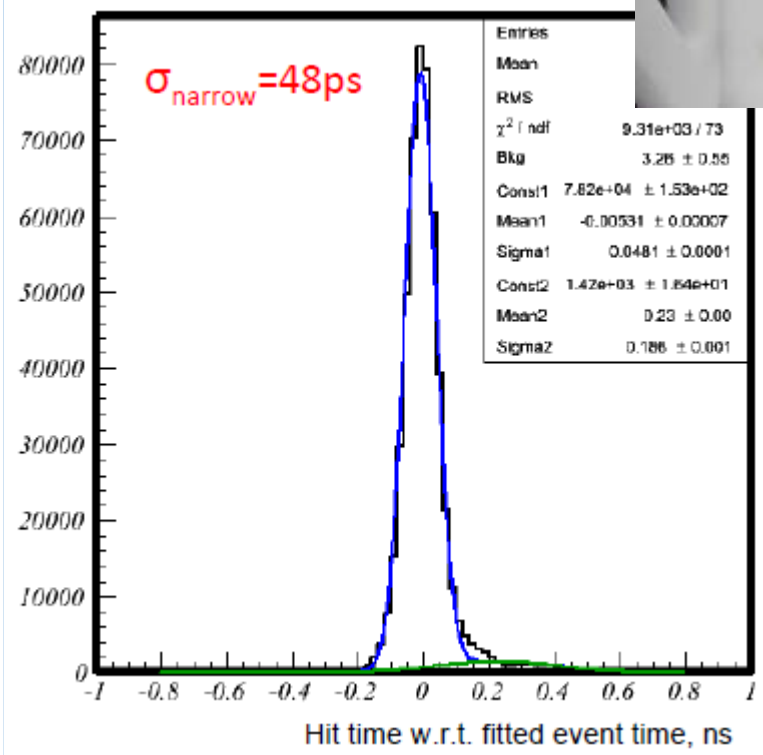
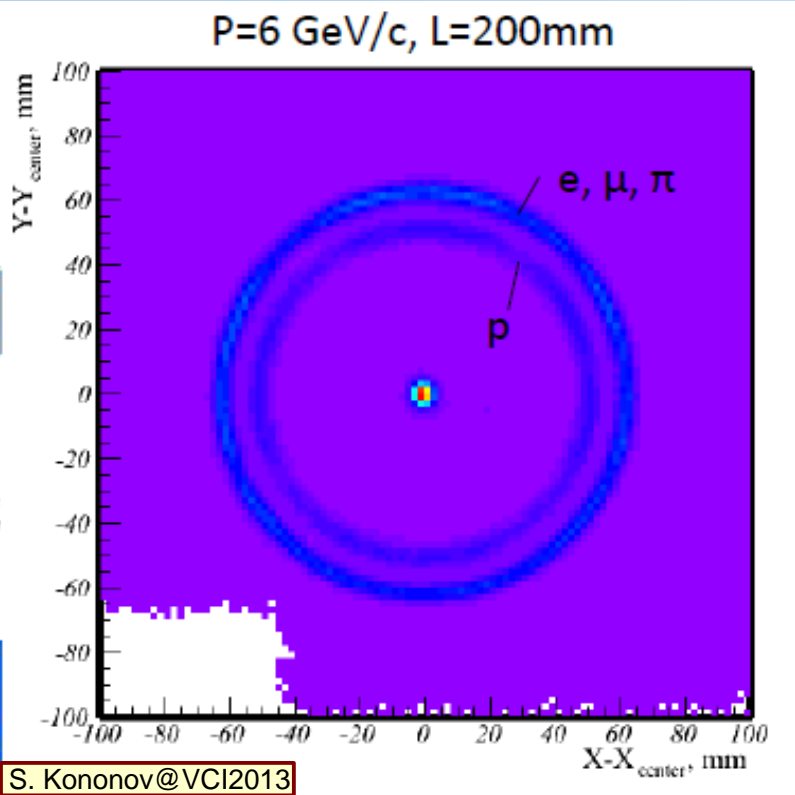
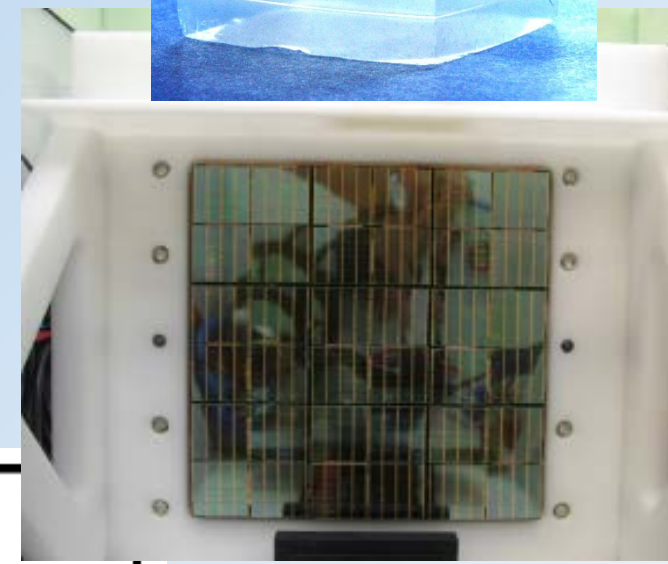
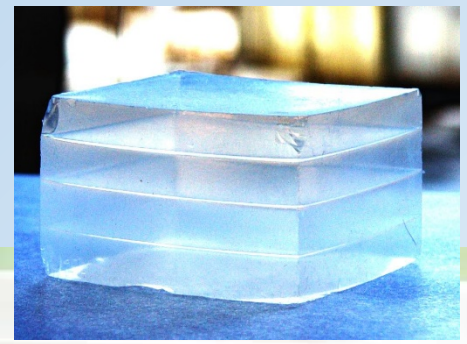




# dSiPM RICH

**FARICH** (Focusing Aerogel RICH) candidate for ALICE, PANDA, Super  $c\text{-}\tau$ , (SuperB):

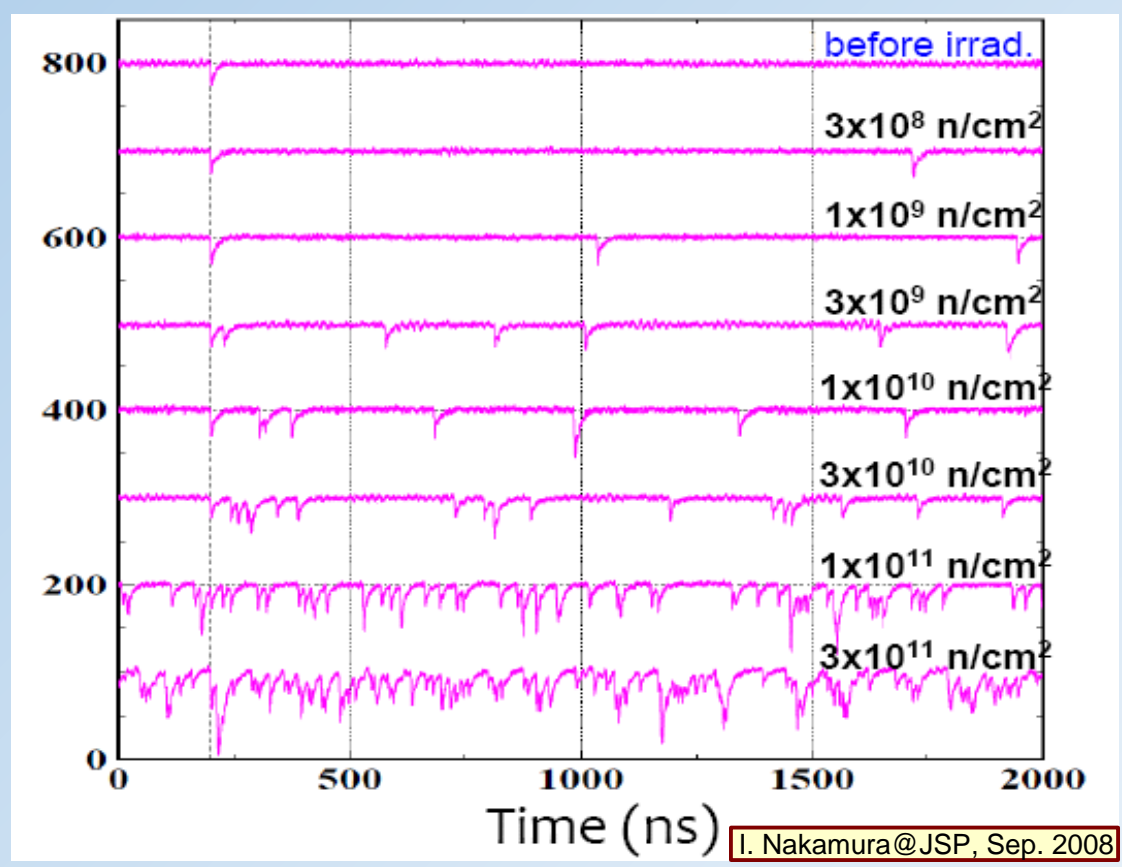
- another focusing aerogel development, 4 layer (37.5 mm,  $n_{max} = 1.046$ )
- dSiPM (DPC3200-22-44) photon detector  $48 \times 48$  pixels ( $20 \times 20 \text{ cm}^2$ )
- first use of digital SiPMs from Philips for RICH
  - tested at CERN beam line (operated at  $-20^\circ$ )
  - excellent single photon timing 48 ps
  - $\approx 14$  photons/ring





# Why didn't we use them? - radiation damage

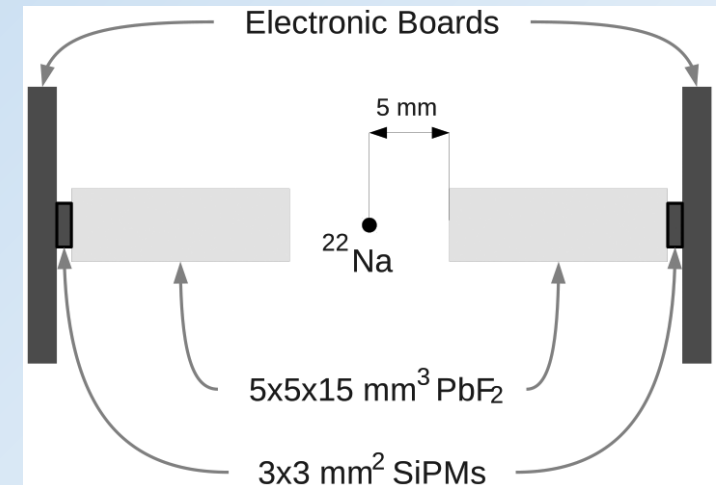
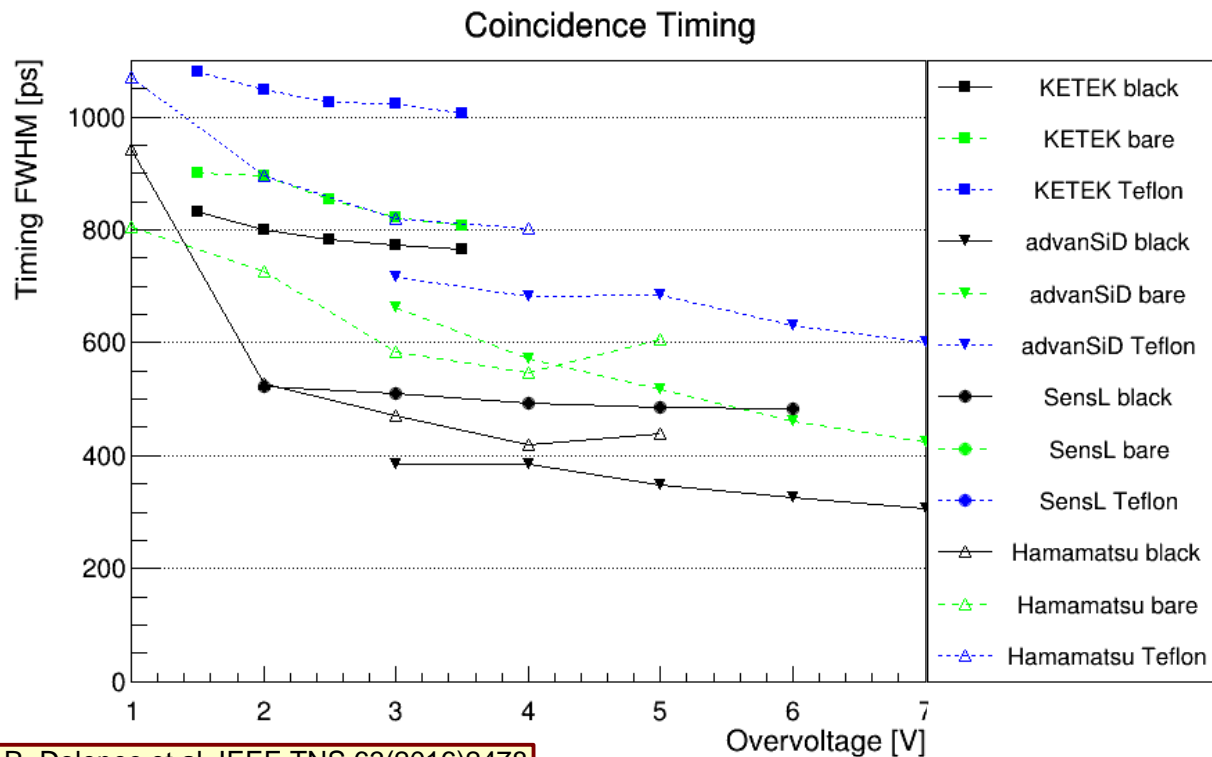
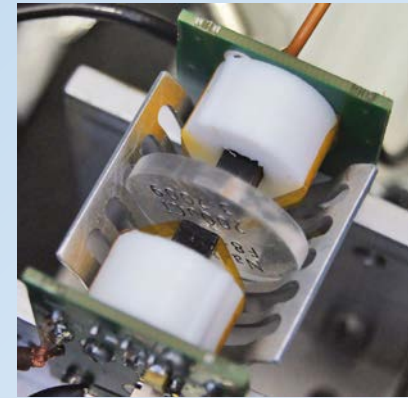
Bulk damage produced by radiation (n, p, ...) increases the dark current proportionally to fluence and eventually signals of Cherenkov photons can not be distinguished from noise.



→ Very hard to use SiPMs as single photon detectors after fluence of  $\approx 10^{11}$  n<sub>1MeV</sub>/cm<sup>2</sup> at room temperature!

# SiPM: TOF-PET timing with Cherenkov light

- 3x3 mm SiPMs from several producers were tested in Cherenkov TOF-PET setup and with pico-second laser source
- 5x5x15 mm<sup>3</sup> PbF<sub>2</sub> polished bare (black painted) crystals
- Teflon crystal support ~10mm deep
- custom board with NEC mPC2710TB amp.
- measured at -25 C<sup>o</sup>
- variation of bias - better PDE and timing
- best CRT achieved was 309 ps FWHM

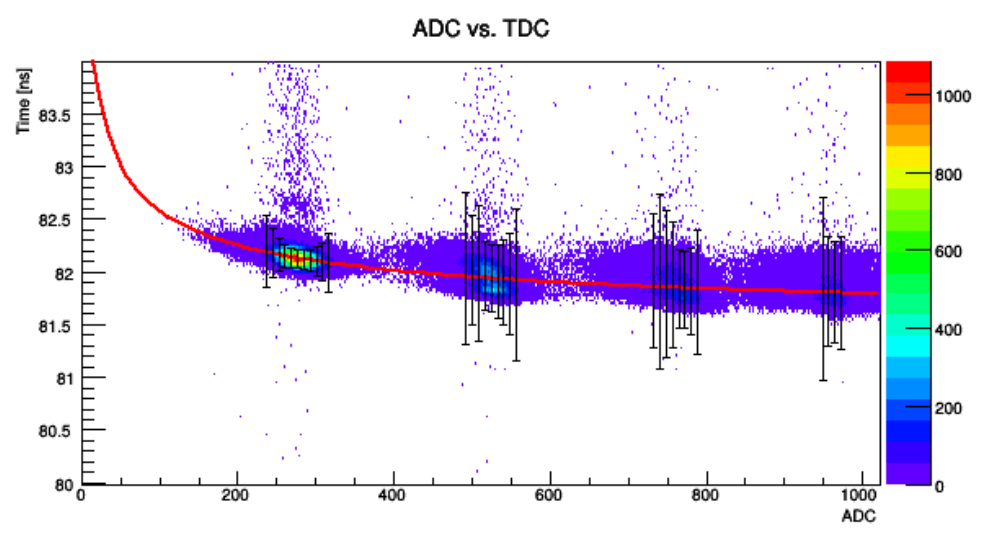
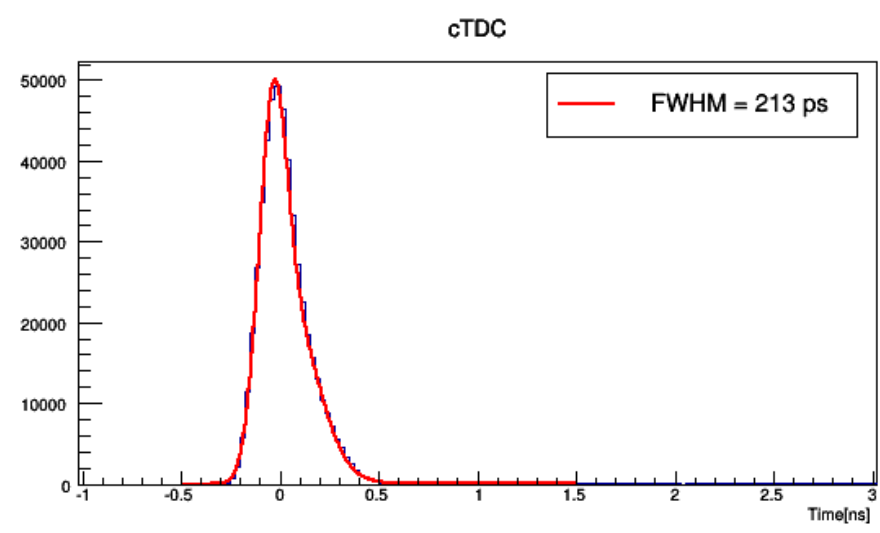
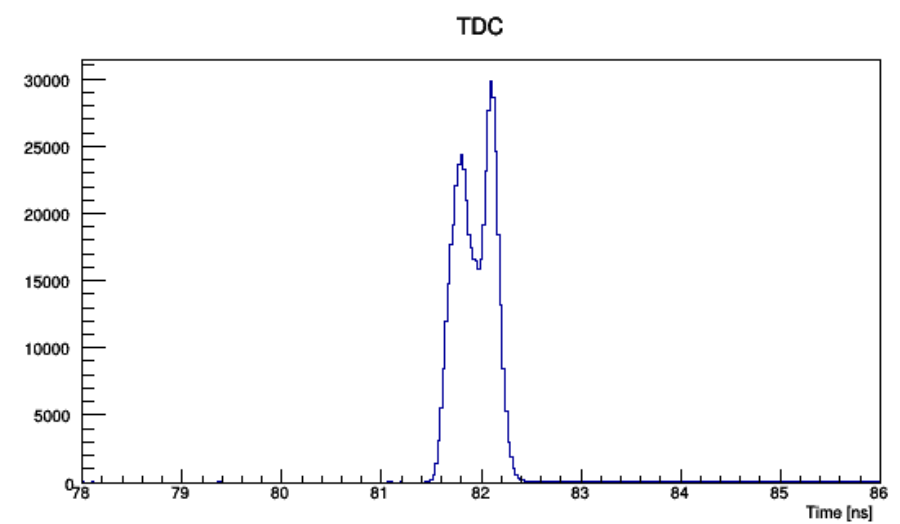
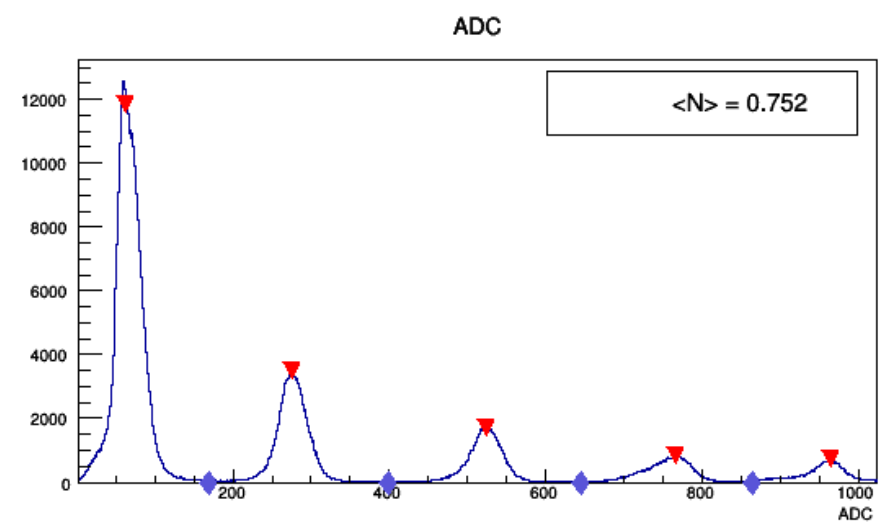


Producer	Model	Pixel Pitch [ $\mu\text{m}$ ]	Breakdown [V]
Hamamatsu	S12641-PA-50	50	65
AdvanSiD	ASD-NUV3S-P-40	40	26
KETEK	PM3375TS-SBO	75	25
SensL	MicroFC-30050-SMT-GP	50	25

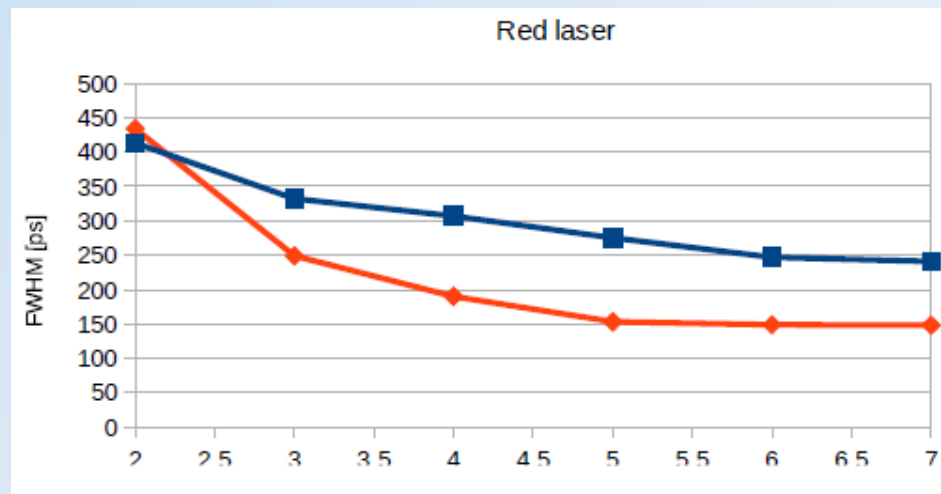
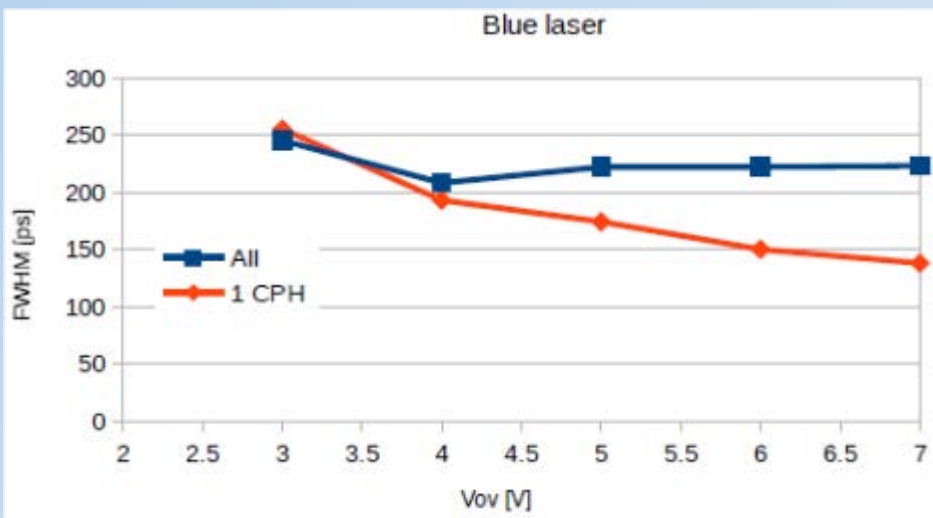
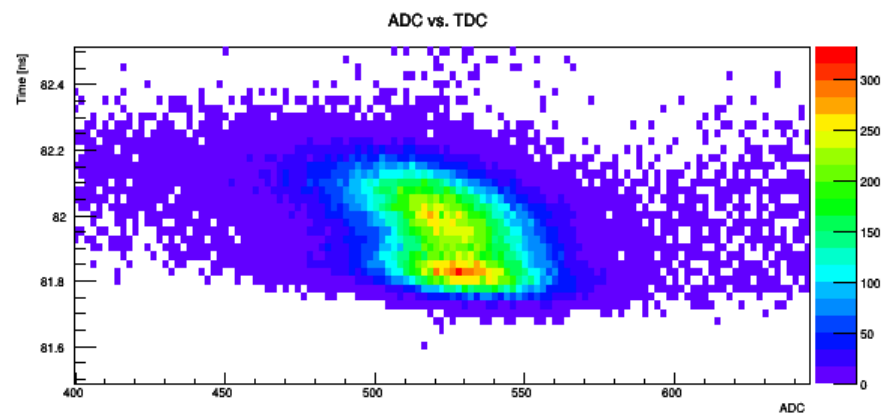
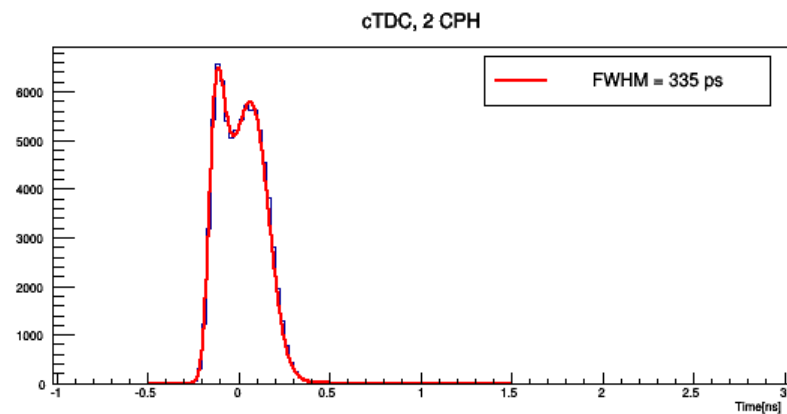
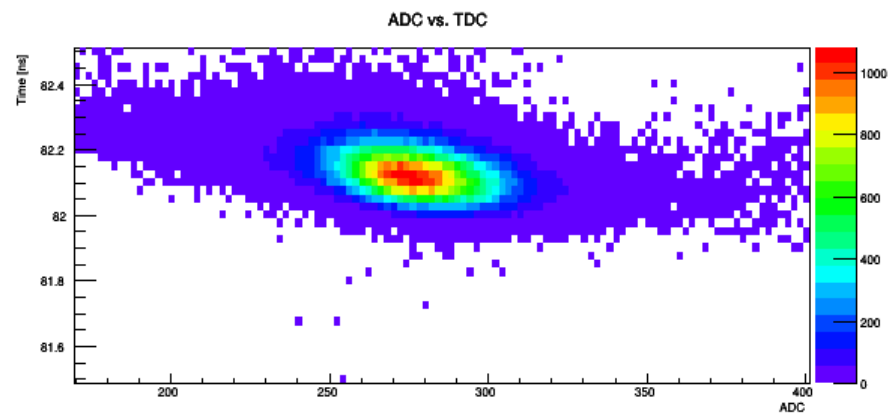
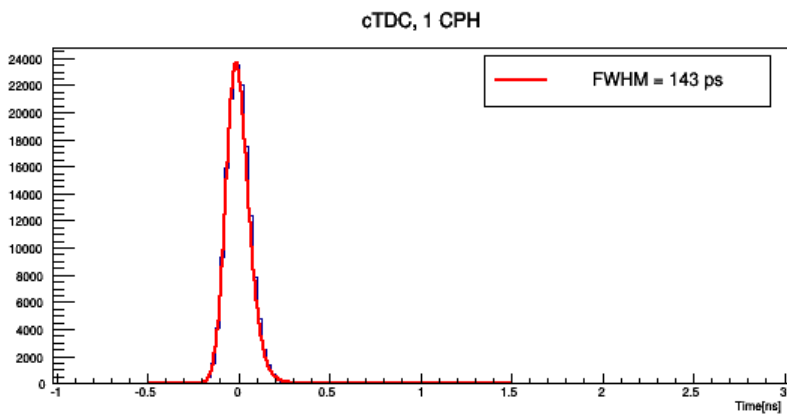
R. Dolenc et al. IEEE TNS 63(2016)2478

# SiPM: timing test with pico-second laser

- AdvanSiD SiPM, OV=6V, T=-25°C
- blue laser  $\lambda = 408\text{nm}$ ,  $\sim 35\text{ps}$  FWHM







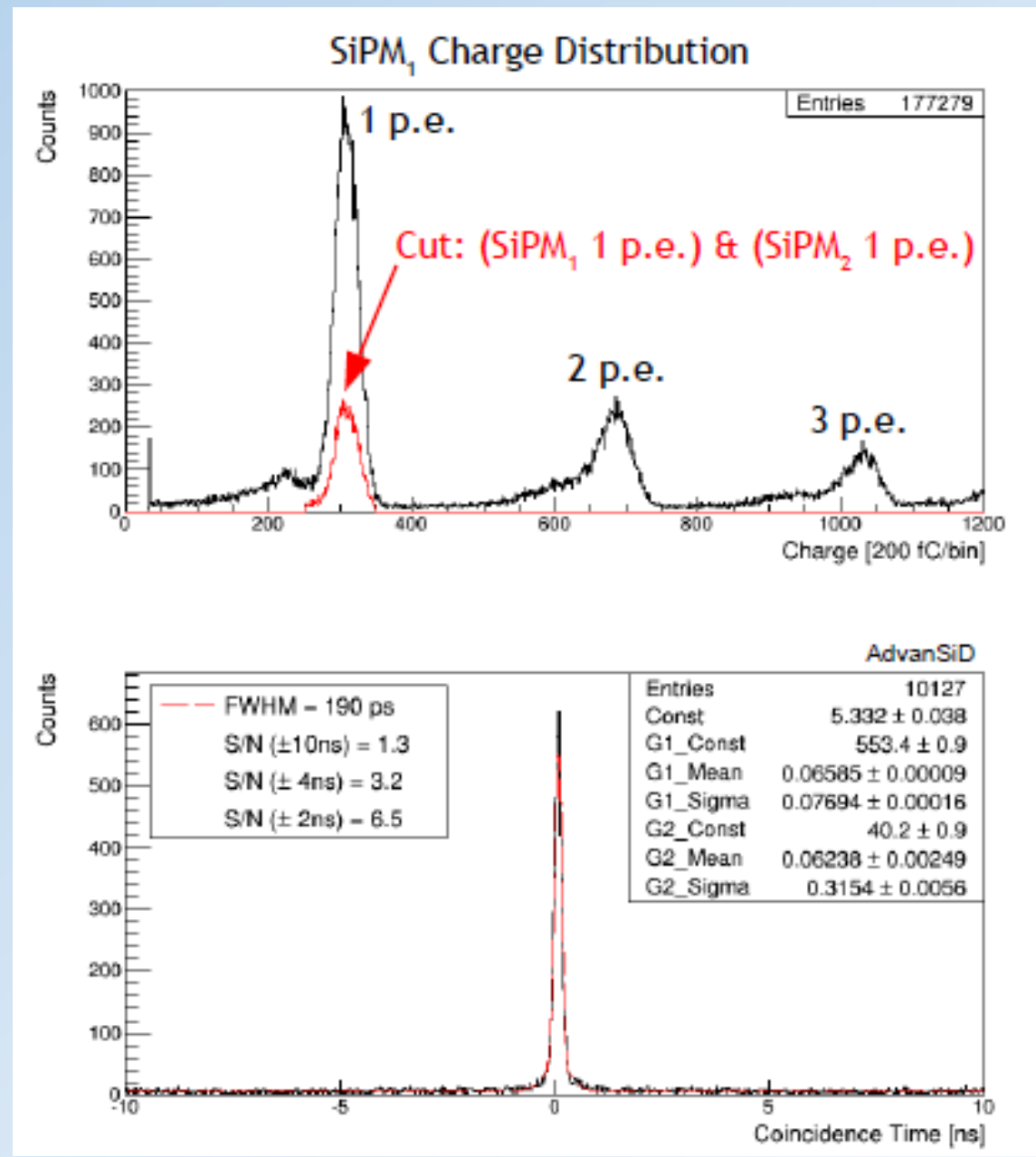
# TOF-PET CRT with only 1 m.c. signals

- Using only events with single micro cell signal:

CRT = 190 ps FWHM

- AdvanSiD,
- $V_{OV} = 7V$ ,
- black-painted  $PbF_2$ ,
- $T = -25^\circ C$

How to improve timing of events with optical cross-talk ?



# Photosensors comparison table



	Peak PDE	QE range	Gain	ENF	single photon?	TTS	B	Rad. Hard.	Ageing
PD	≈ 100%	UV-IR	1	1	NO	-	OK	OK	OK
APD	≈ 80%		< 1000	> 2	NO	-			
SiPM	≈ 60%	UV-IR	≈ 10 <sup>6</sup>	≈ 1 – 1.2	YES (dark counts?)	≈ 50ps	OK	OK (gain, noise?)	OK
PMT	≈ 35%	UV-IR	≈ 10 <sup>7</sup>	≈ 1.1 – 1.5	YES	≈ 200ps	≈ 0.1 mT	HIGH	OK
MA-PMT			≈ 10 <sup>7</sup>	≈ 1.1 – 1.5		≈ 150ps	≈ 10 mT		
MESH-PMT			≈ 10 <sup>6</sup>	≈ 1.1 – 2		≈ 100ps	≈ 2 T (axial)		
MCP-PMT	≈ 25%	UV-IR	≈ 10 <sup>6</sup>	≈ 1.1 – 2	YES	≈ 20ps	≈ 2 T (axial)	HIGH	OK? (ALD)
VPT	≈ 25%	UV-IR	≈ 10	≈ 2	NO	-	≈ 2 T (axial)	OK	OK
HPD	≈ 40%		≈ 5000	≈ 1 – 1.1	NO	-	OK (axial)		
HAPD	≈ 40%		≈ 10 <sup>5</sup>	≈ 1 – 1.1	YES	≈ 30ps (@high gain)			
CsI MWPC	≈ 25%	UV	≈ 10 <sup>5</sup>	≈ 2	YES	≈ 10ns	OK	HIGH	IBF?
CsI MPGD	≈ 20%	UV	≈ 10 <sup>6</sup>	≈ 1.2 – 2	YES	≈ 100ps			



- SiPMs have some very nice properties: low operation voltage, high PDE, high gain, excellent timing, insensitive to magnetic field, easy to operate, not damaged by operation at ambient light ...,
- but also some **drawbacks for single photon detections**: high dark count rate, sensitive to neutron irradiation.
  
- To use SiPMs to detect single Cherenkov photons timing information is used to increase S/N.
- Light concentrators can further improve S/N
- **Main problem is increase of dark count rate with neutron irradiation!**
- Currently the only solution seems to be operation at cryogenic temperature.
  
- Intrinsic timing resolution ( $< 20$  ps) is comparable to MCP-PMT but timing resolution of SiPM is affected by large device capacitance and optical cross-talk effects.